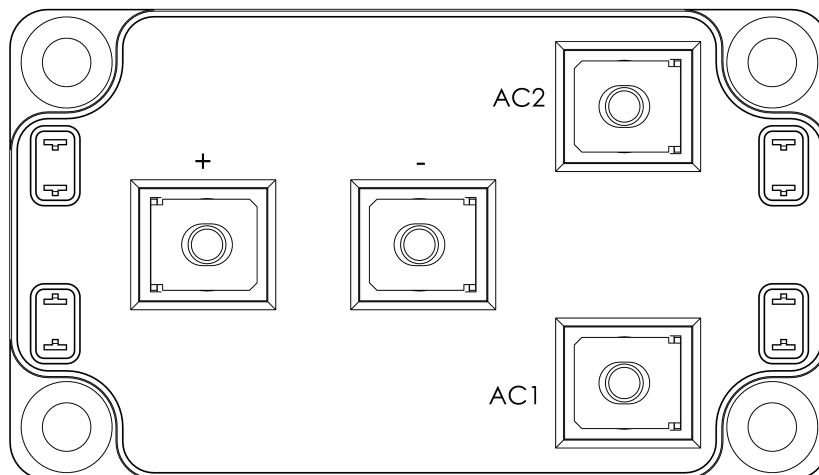
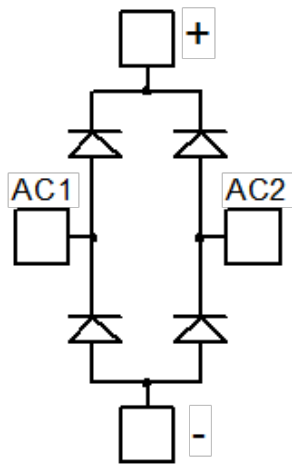



MSCDC200H120AG SiC Diode Full Bridge Power Module

1 Product Overview

This section shows the product overview for the MSCDC200H120AG device.



All ratings at $T_j = 25^\circ\text{C}$, unless otherwise specified.

 **Caution:** These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.

1.1 Features

The following are key features of the MSCDC200H120AG device:

- Silicon Carbide (SiC) Schottky Diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature Independent switching behavior
 - Positive temperature coefficient on VF
- High blocking voltage
- Low stray inductance
- M5 power connectors
- Aluminum Nitride (AlN) substrate for improved thermal performance

1.2 Benefits

The following are benefits of the MSCDC200H120AG device:

- Outstanding performance at high-frequency operation
- Low losses
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- RoHS compliant

1.3 Applications

The MSCDC200H120AG device is designed for the following applications:

- Uninterruptible Power Supply (UPS)
- Induction heating
- Welding equipment
- High-speed rectifiers

2 Electrical Specifications

This section shows the electrical specifications for the MSCDC200H120AG device.

2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings per diode for the MSCDC200H120AG device.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter	Maximum Ratings	Unit
V_{RRM}	Repetitive peak reverse voltage	1200	V
I_F	DC forward current	$T_C = 95\text{ }^\circ\text{C}$ 200	A

The following table shows the thermal and package characteristics of the MSCDC200H120AG.

Table 2 • Thermal and Package Characteristics

Symbol	Characteristic	Min	Max	Unit		
V_{ISOL}	RMS isolation voltage, any terminal to case $t = 1$ minute, 50 Hz/60 Hz	4000		V		
T_J	Operating junction temperature range	-40	175	$^\circ\text{C}$		
T_{JOP}	Recommended junction temperature under switching conditions	-40	$T_{Jmax} - 25$			
T_{STG}	Storage temperature range	-40	125			
T_C	Operating case temperature	-40	125			
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
W_t	Package weight			300	g	

2.2 Electrical Performance

The following table shows the electrical characteristics per diode of the MSCDC200H120AG.

Table 3 • Electrical Characteristics Per Diode

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Diode forward voltage	$I_F = 200\text{ A}$	$T_J = 25\text{ }^\circ\text{C}$	1.5	1.8	V
			$T_J = 175\text{ }^\circ\text{C}$	2.1		
I_{RM}	Reverse leakage current	$V_R = 1200\text{ V}$	$T_J = 25\text{ }^\circ\text{C}$	60	800	μA
			$T_J = 175\text{ }^\circ\text{C}$	1000		
Q_C	Total capacitive charge	$V_R = 600\text{ V}$		896		nC
C	Total capacitance	$f = 1\text{ MHz}, V_R = 400\text{ V}$		984		pF
		$f = 1\text{ MHz}, V_R = 800\text{ V}$		728		
R_{thJC}	Junction to case thermal resistance				0.16	$^\circ\text{C/W}$

2.3 Performance Curves

This section shows the typical performance curves for the MSCDC200H120AG device.

Figure 1 • Maximum Transient Thermal Impedance

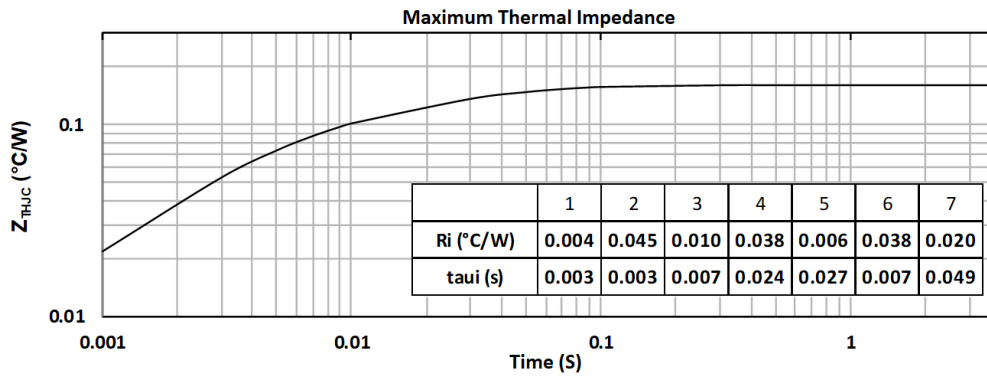


Figure 2 • Forward Current vs Forward Voltage

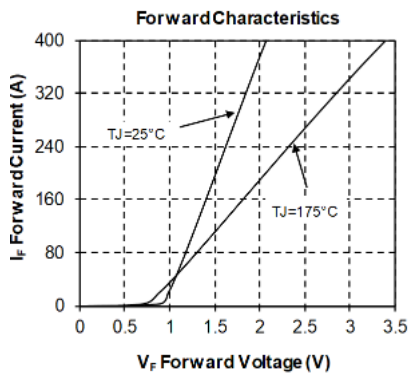
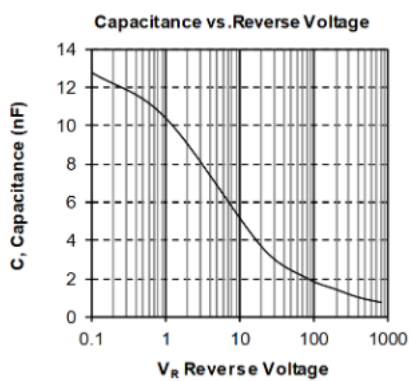


Figure 3 • Capacitance vs. Reverse Voltage



3 Package Specification

This section shows the package specification for the MSCDC200H120AG device.

3.1 Package Outline Drawing

This section shows the package outline drawing of the MSCDC200H120AG device. The dimensions in the following figure are in millimeters.

Figure 4 • Package Outline Drawing

